

Description

The HSM4606B is the high performance complementary N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

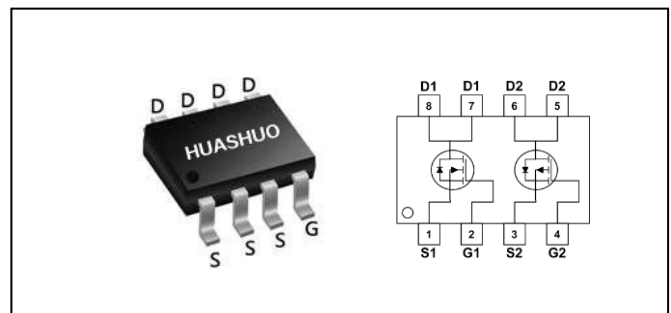
The HSM4606B meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

BVDSS	RDSON	ID
30V	18mΩ	7A
-30V	24mΩ	-7A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V _{DS}	Drain-Source Voltage	30	-30	V
V _{GS}	Gate-Source Voltage	±20	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	7	-7	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	5.6	-5.6	A
I _{DM}	Pulsed Drain Current ²	28	-28	A
P _D @T _A =25°C	Total Power Dissipation ⁴	2	2	W
T _{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	110	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	50	°C/W



N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.023	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =6A	---	18	26	mΩ
		V _{GS} =4.5V, I _D =4A	---	27	35	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.6	2.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =6A	---	12	---	S
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _D =5A	---	5.5	---	nC
Q _{gs}	Gate-Source Charge		---	0.9	---	
Q _{gd}	Gate-Drain Charge		---	1.4	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3Ω I _D =5A	---	4.7	---	ns
T _r	Rise Time		---	2.6	---	
T _{d(off)}	Turn-Off Delay Time		---	14	---	
T _f	Fall Time		---	3.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	288	---	pF
C _{oss}	Output Capacitance		---	42	---	
C _{rss}	Reverse Transfer Capacitance		---	38	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	0.75	1.4	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.021	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-6A	---	24	35	mΩ
		V _{GS} =-4.5V, I _D =-4A	---	30	54	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.8	-1.3	-2.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-6A	---	15	---	S
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V, I _D =-4A	---	12.6	---	nC
Q _{gs}	Gate-Source Charge		---	5.5	---	
Q _{gd}	Gate-Drain Charge		---	3.3	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-10V, R _G =3.3Ω, I _D =-4A	---	8.4	---	ns
T _r	Rise Time		---	13	---	
T _{d(off)}	Turn-Off Delay Time		---	75	---	
T _f	Fall Time		---	12	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	906	---	pF
C _{oss}	Output Capacitance		---	109	---	
C _{rss}	Reverse Transfer Capacitance		---	87	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	-0.78	-1.5	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



N-Channel Typical Characteristics

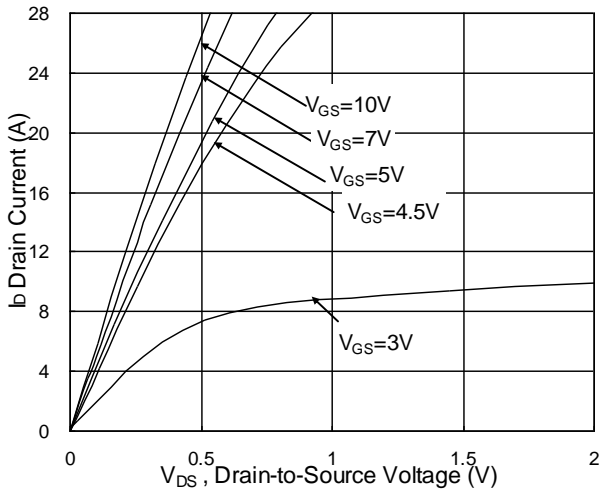


Fig.1 Typical Output Characteristics

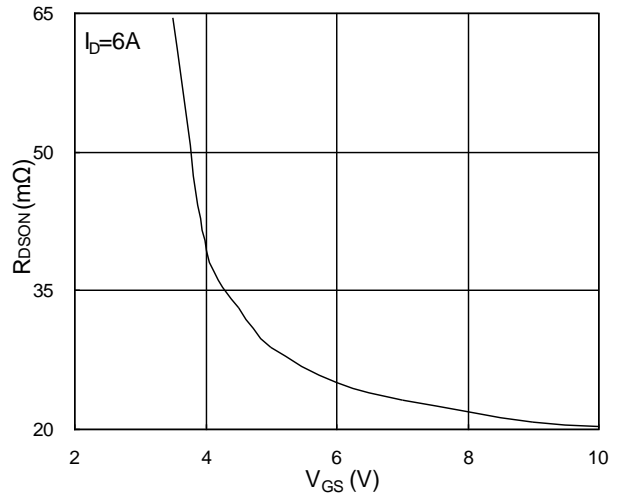


Fig.2 On-Resistance vs. Gate-Source

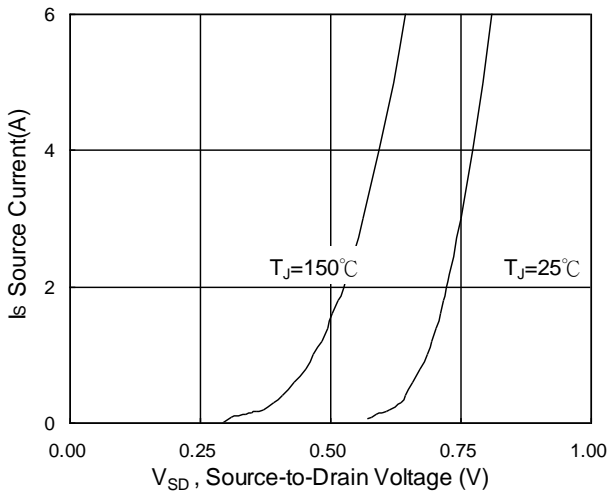


Fig.3 Forward Characteristics Of Reverse

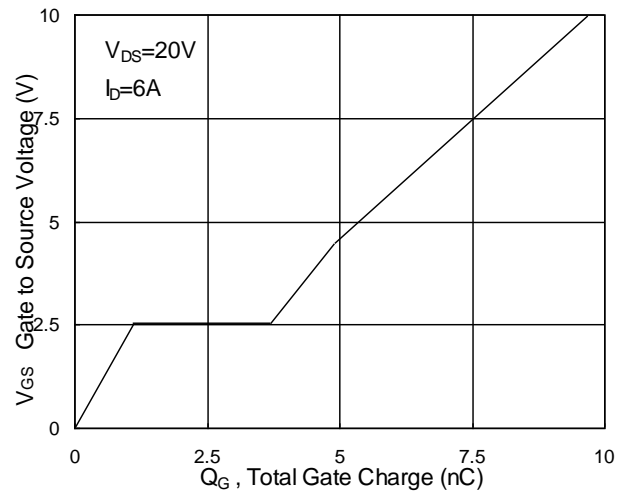


Fig.4 Gate-Charge Characteristics

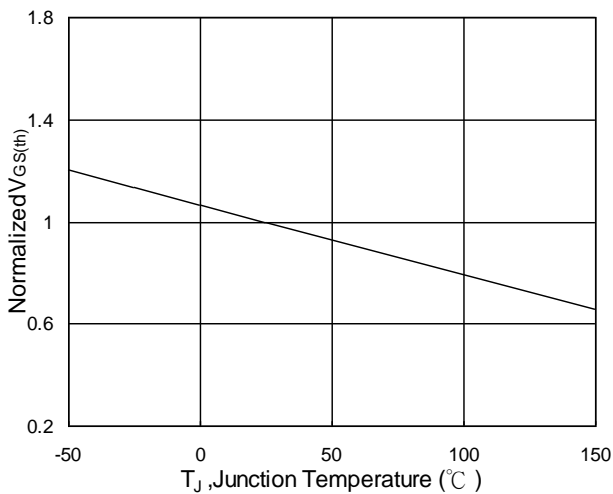


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

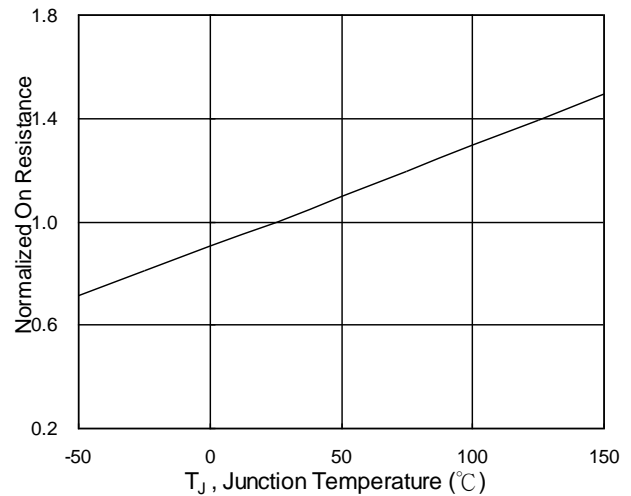


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

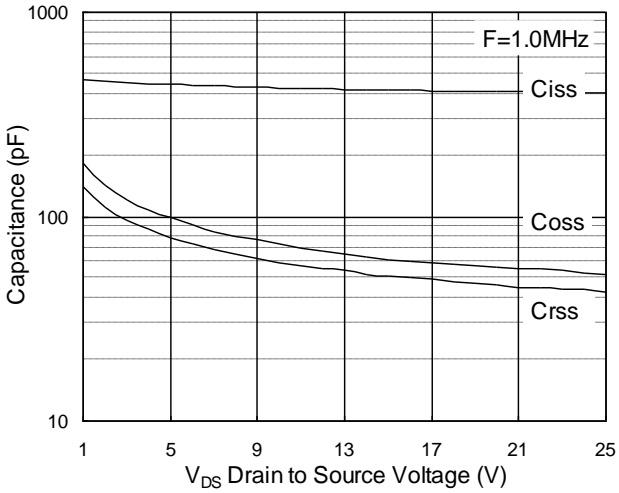


Fig.7 Capacitance

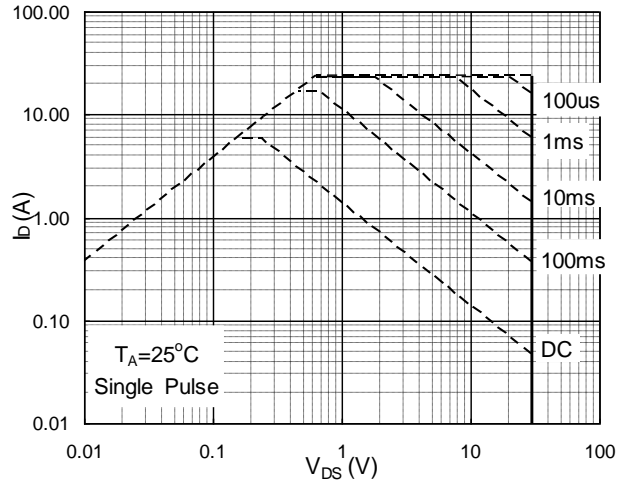


Fig.8 Safe Operating Area

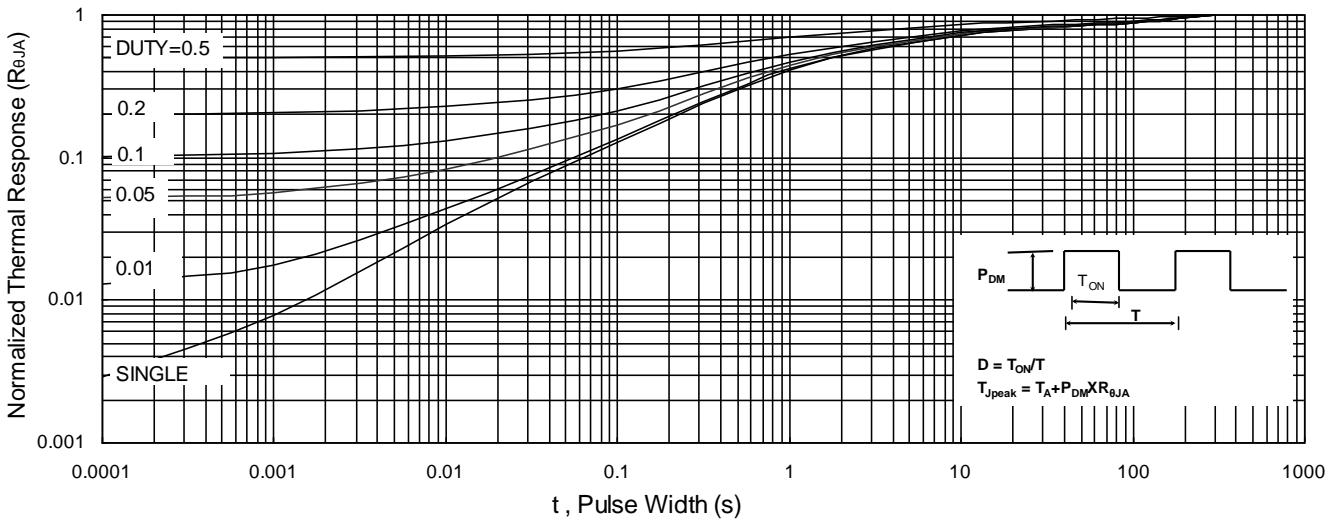


Fig.9 Normalized Maximum Transient Thermal Impedance

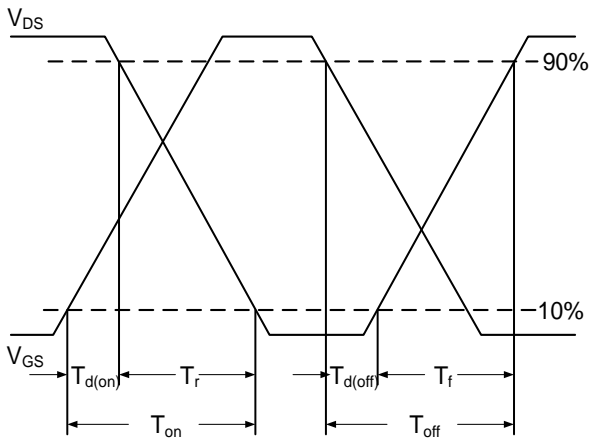


Fig.10 Switching Time Waveform

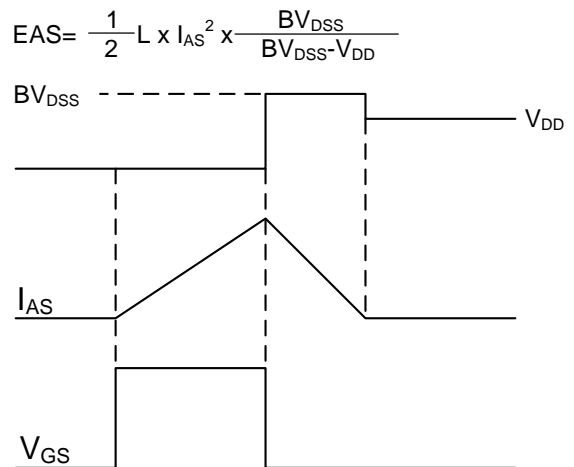


Fig.11 Unclamped Inductive Switching



P-Channel Typical Characteristics

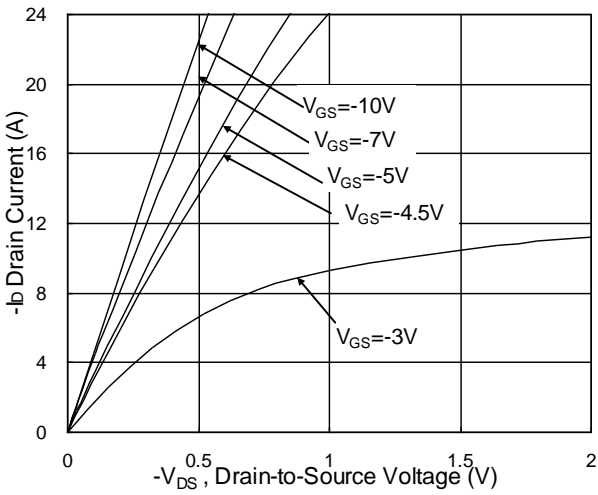


Fig.1 Typical Output Characteristics

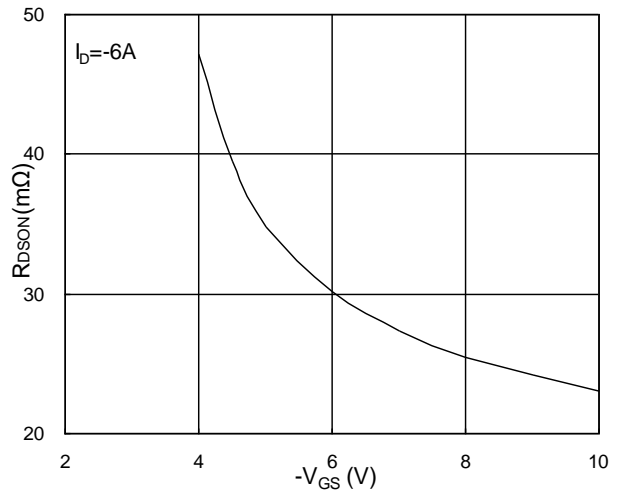


Fig.2 On-Resistance v.s Gate-Source

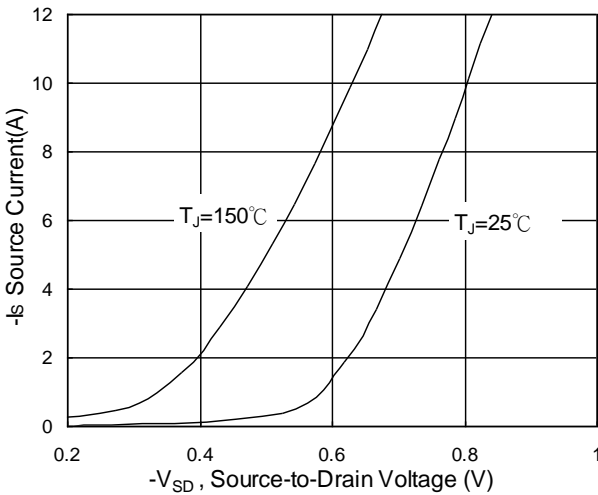


Fig.3 Forward Characteristics Of Reverse

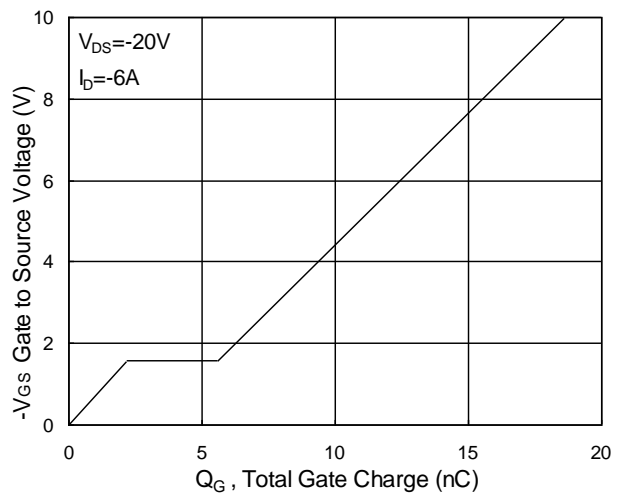


Fig.4 Gate-Charge Characteristics

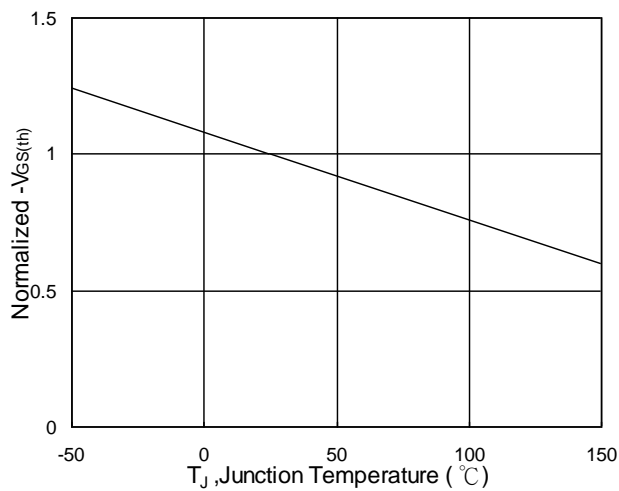


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

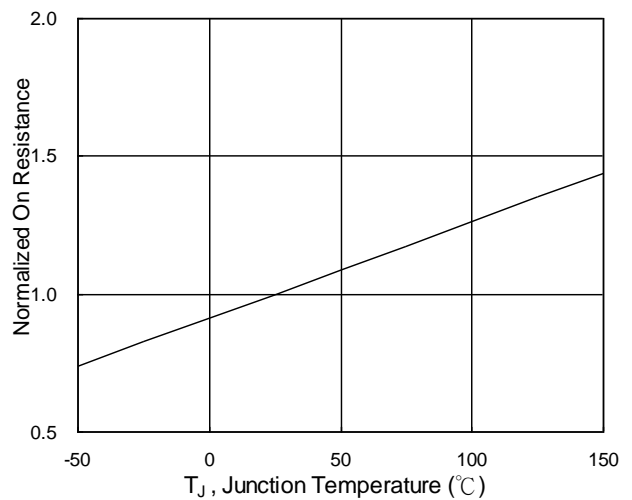


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

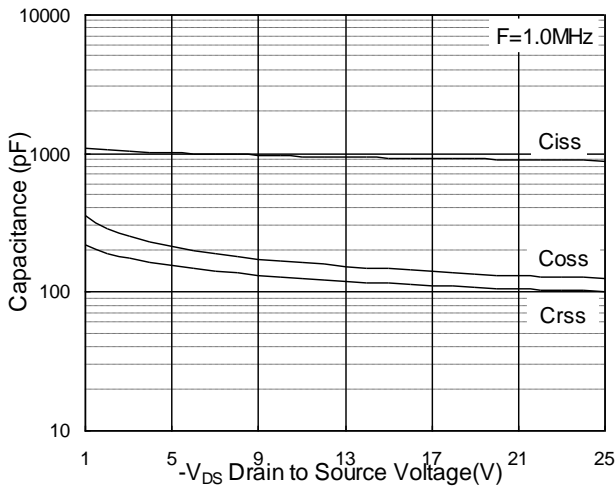


Fig.7 Capacitance

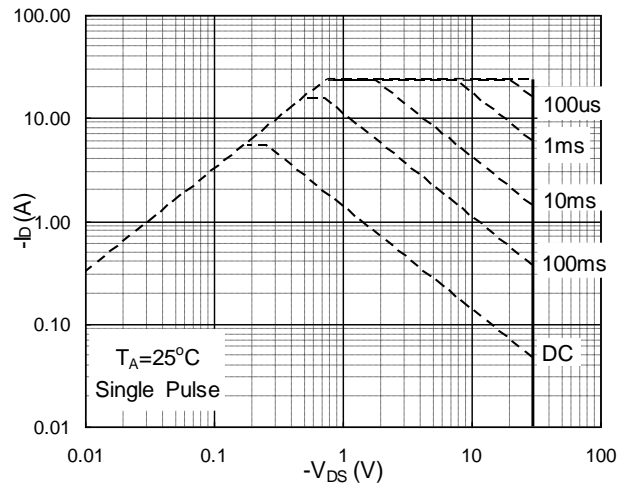


Fig.8 Safe Operating Area

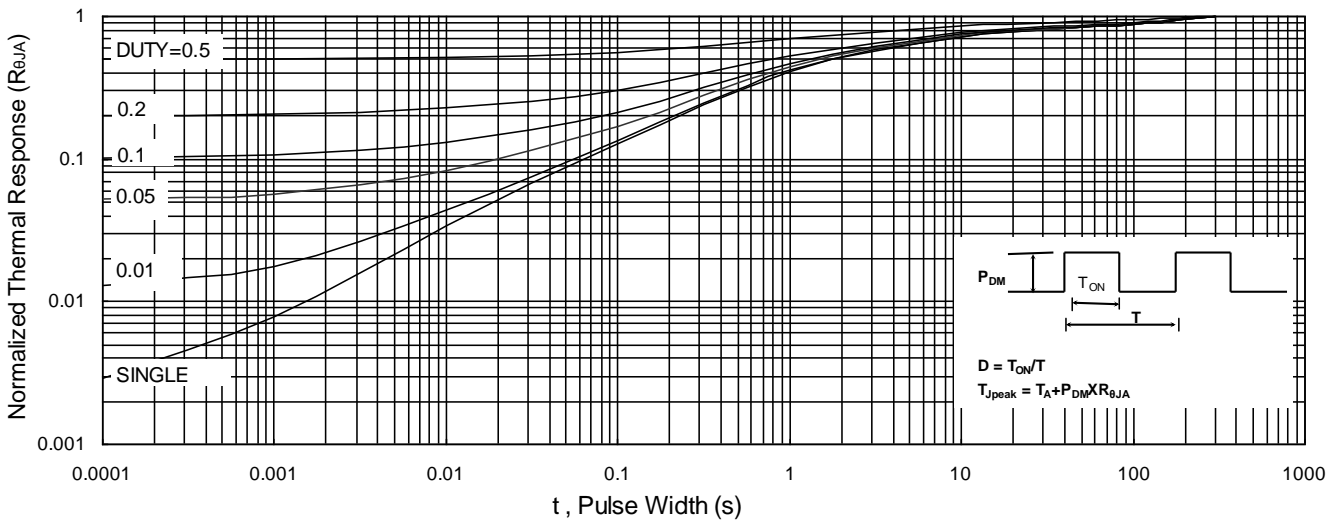


Fig.9 Normalized Maximum Transient Thermal Impedance

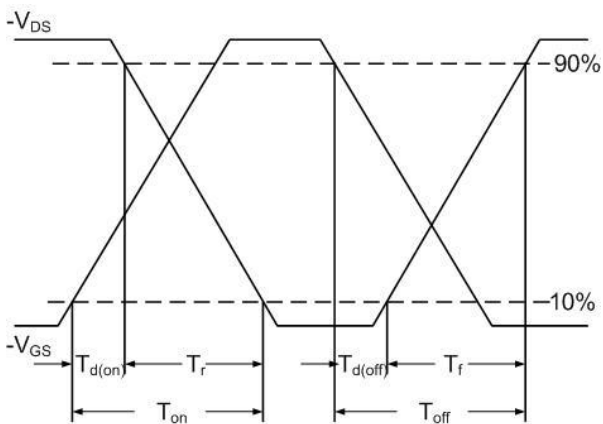


Fig.10 Switching Time Waveform

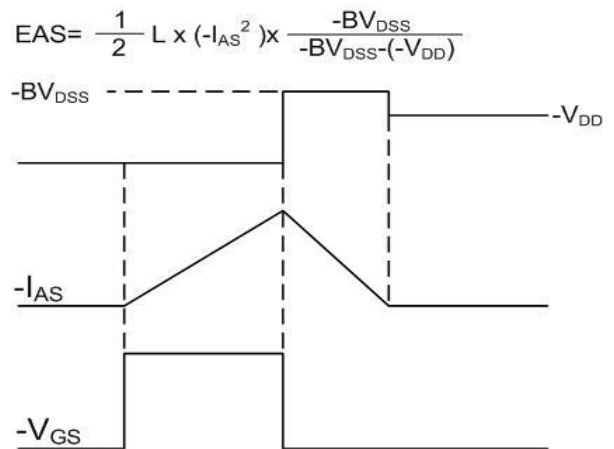
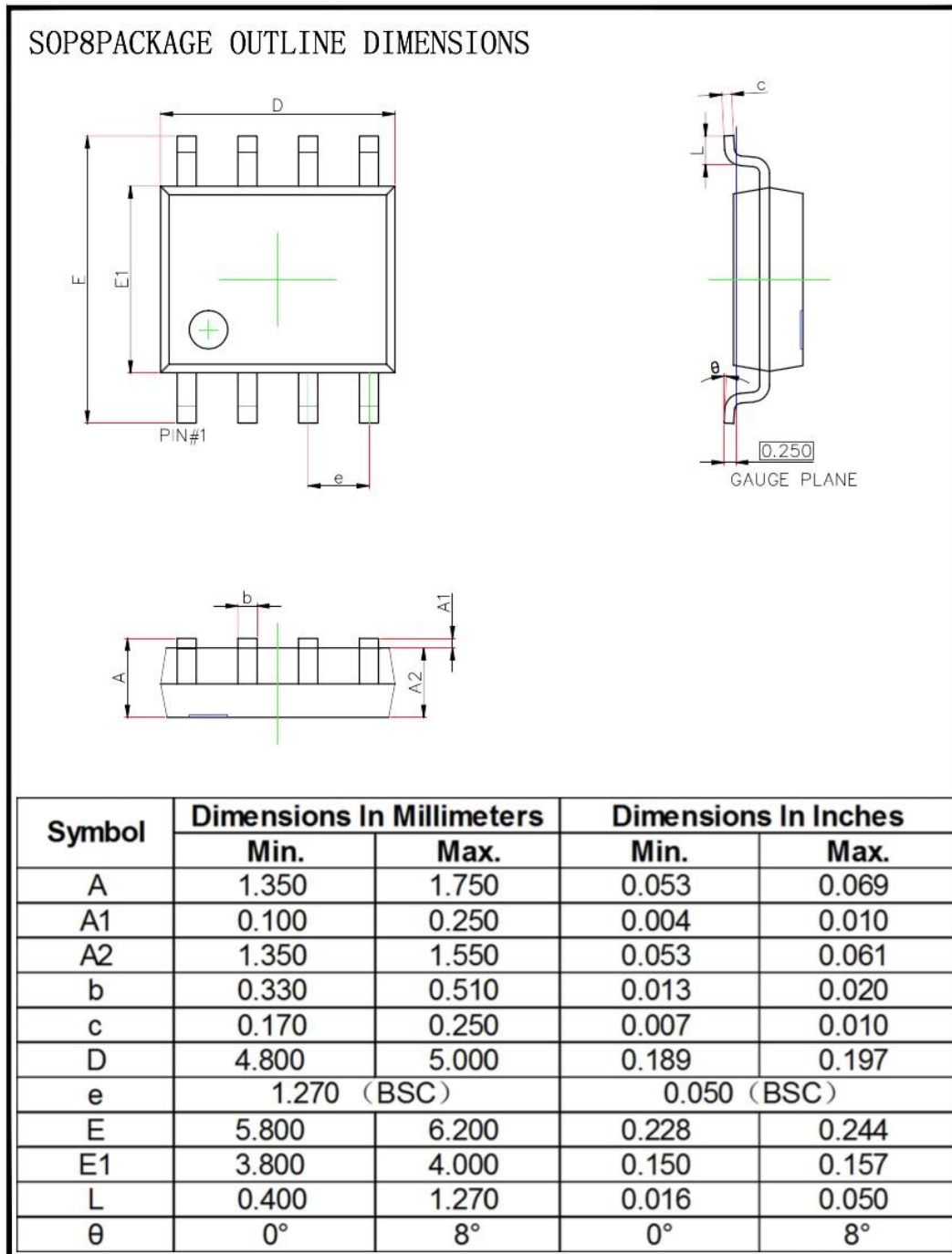


Fig.11 Unclamped Inductive Switching



Ordering Information

Part Number	Package code	Packaging
HSM4606B	SOP-8	4000/Tape&Reel



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